

## KSC2310

### **High Voltage Power Amplifier**

- Collector-Base Voltage: V<sub>CBO</sub>=200V
  Current Gain Bandwidth Product: f<sub>T</sub>=100MHz



1. Emitter 2. Collector 3. Base

## **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	200	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	50	mA
P <sub>C</sub>	Collector Power Dissipation	800	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	200			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C=5mA$ , $I_B=0$	150			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =200V, I <sub>E</sub> =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	40		240	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =30V, I <sub>C</sub> =10mA		100		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		3.5	5	pF

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240

# **Typical Characteristics**

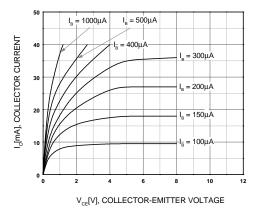


Figure 1. Static Characteristic

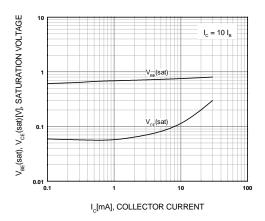


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

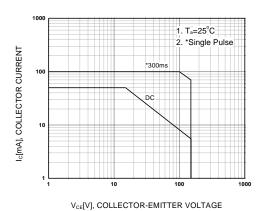
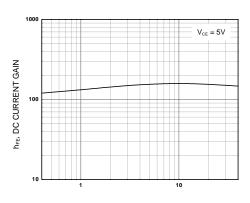


Figure 5. Safe Operating Area



 $I_{\text{c}}[\text{mA}]$ , COLLECTOR CURRENT

Figure 2. DC current Gain

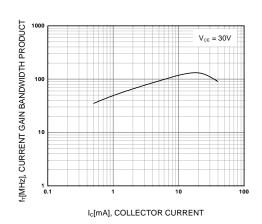


Figure 4. Current Gain Bandwidth Product

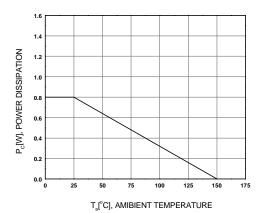
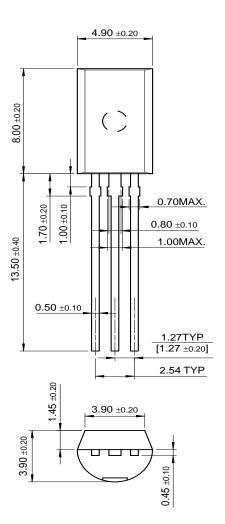


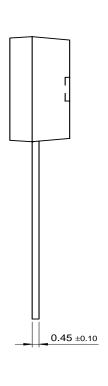
Figure 6. Power Derating

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# **Package Demensions**

# TO-92L





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